



News Release / Presseinformation

Infineon Introduces 5th Generation thinQ!TM SiC Schottky Barrier Diodes Delivering Market Leading Efficiency at Attractive Price-Performance Ratio

Neubiberg, Germany – September 26, 2012 – Infineon today announces the expansion of its SiC (Silicon Carbide) portfolio with the introduction of the 650V thinQ!TM SiC Schottky Barrier Diodes Generation 5.

Infineon's proprietary diffusion soldering process, already introduced with Generation 3, is now combined with a new, more compact design as well as latest advancements in thin wafer technology bringing improved thermal characteristics and a Figure of Merit ($Q_c \times V_f$) in the order of 30% lower with respect to the preceding Infineon SiC diode families. The result is a series of products delivering improved efficiency in PFC and Boost stages over all load conditions with respect to all previous thinQ!TM generations. The Generation 5 products are targeted for use in high-end Server and Telecom SMPS (Switched-Mode Power Supply), PC Silverbox and Lighting applications, Solar Inverters and UPS (Uninterruptible Power Supply) systems. With the new generation, these applications not only benefit from improved efficiency, but also from reduced EMI (Electromagnetic Interference), increased system reliability and cost/size savings due to reduced cooling requirements.

"Infineon has significantly improved and expanded the portfolio since the first introduction of its SiC Schottky diodes in 2001. SiC diodes are differentiating products, shaping the future of green energy," says Jan-Willem Reynaerts, Product Segment Head High Voltage Power Conversion at Infineon Technologies. "The Generation 5 enables further improvements in system efficiency and power density compared to previous generations, in combination with an attractive price-performance ratio."

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Media Relations:
Worldwide Headquarters
U.S.A.
Asia
Japan
Investor Relations

Name:
Tillmann Geneuss
Mitch Ahiers
Chi Kang David Ong
Yoko Sasaki
EU/APAC/USA/CAN

Phone:
+49 89 234 83346
+1 408 503 2791
+65 6876 3070
+81 3 5745 7340
+49 89 234 26655

Email:
tillmann.geneuss@infineon.com
mitch.ahiers@infineon.com
david.ong@infineon.com
yoko.sasaki@infineon.com
investor.relations@infineon.com

The low capacitive charge (Q_c) values of Generation 3 combined with the forward voltage (V_f) levels of Generation 2 allow Generation 5 to deliver utmost efficiency levels in PFC circuits. The new family has a higher breakdown voltage level: 650V instead of the 600V of Generation 2 and 3, matching the latest releases in CoolMOS™ technology. This feature provides higher safety margins in applications like Solar Inverters and in challenging SMPS environments. Generation 5 offers moreover a high robustness against surge currents and a broader portfolio including products with both higher current ratings and new packages, such as TO-247 and ThinPAK.

Availability

Samples are available now.

Further information on Infineon's new 650V thinQ!™ SiC Schottky Barrier Diodes Generation 5 is available at www.infineon.com/sic-gen5

About Infineon

[Infineon](http://www.infineon.com) Technologies AG, Neubiberg, Germany, offers semiconductor and system solutions addressing three central challenges to modern society: [energy efficiency](#), [mobility](#), and [security](#). In the 2011 fiscal year (ending September 30), the company reported sales of Euro 4 billion with close to 26,000 employees worldwide. Infineon is listed on the Frankfurt Stock Exchange (ticker symbol: IFX) and in the USA on the over-the-counter market OTCQX International Premier (ticker symbol: IFNNY).

Further information is available at www.infineon.com

This news release is available online at www.infineon.com/press

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